

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A semiconductor device comprising:
 - a light-transmitting substrate;
 - a base film having a projection, the film being formed over one surface of the light-transmitting substrate;
 - an island-like semiconductor layer having a crystal structure covering the projection and extending over a pair of edges of the projection;
 - a gate insulating film over the island-like semiconductor layer; and
 - a gate electrode over the gate insulating film.

2. (Currently Amended) A semiconductor device comprising a light-transmitting substrate and a thin film transistor over the light-transmitting substrate, wherein
 - a base film having a projection is provided over one surface of the light-transmitting substrate;
 - an ~~island-like semiconductor~~ island-like semiconductor comprising a channel formation region, at least a part of the channel formation region of the thin film transistor is provided over the projection,
 - the island-like semiconductor layer covers the projection and extends over a pair of edges of the projection;
 - a gate insulating film over the island-like semiconductor layer; and
 - a gate electrode over the gate insulating film.

3. (Previously Presented) A semiconductor device according to claim 1, wherein a height of the projection is 30 to 100 nm.

4. (Previously Presented) A semiconductor device according to claim 2, wherein a height of the projection is 30 to 100 nm.

5.-10. (Canceled)

11. (Previously Presented) A semiconductor device comprising:

a light-transmitting substrate;

a base film having a region of a first thickness and a region of a second thickness smaller than the first thickness, the film being formed over one surface of the light-transmitting substrate, and the region of the first thickness having an area smaller than the region of the second thickness;

an island-like semiconductor layer having a crystal structure over the base film, the layer being formed over the region of the first thickness and the region of the second thickness,

a gate insulating film over the island-like semiconductor layer; and

a gate electrode over the gate insulating film,

wherein the island-like semiconductor layer is capable of being irradiated with light from another surface of the light-transmitting substrate through the region of the first thickness and the region of the second thickness.

12. (Previously Presented) A semiconductor device comprising a light-transmitting substrate and a thin film transistor over the light-transmitting substrate, wherein

a base film having a region of a first thickness and a region of a second thickness smaller than the first thickness is provided over one surface of the light-transmitting substrate;

the region of the first thickness has an area smaller than the region of the second thickness;

at least a part of a channel formation region of the thin film transistor is provided over the region of the first thickness;

source and drain regions of the thin film transistor are provided over the projection and cover a pair of edges of the projection,

the island-like semiconductor layer is capable of being irradiated with light from another surface of the light-transmitting substrate through the region of the first thickness and the region of the second thickness;

a gate insulating film over the island-like semiconductor layer; and

a gate electrode over the gate insulating film.

13. (Previously Presented) A semiconductor device according to claim 11, wherein a difference in film thickness between the region of the first thickness and the region of the second thickness is 30 to 100 nm.

14. (Previously Presented) A semiconductor device according to claim 12, wherein a difference in film thickness between the region of the first thickness and the region of the second thickness is 30 to 100 nm.

15. (New) A semiconductor device according to claim 1, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

16. (New) A semiconductor device according to claim 2, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

17. (New) A semiconductor device according to claim 11, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

18. (New) A semiconductor device according to claim 12, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

19. (New) A semiconductor device according to claim 1, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.

20. (New) A semiconductor device according to claim 2, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.

21. (New) A semiconductor device according to claim 11, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.

22. (New) A semiconductor device according to claim 12, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.